

STARPOWER

SEMICONDUCTOR

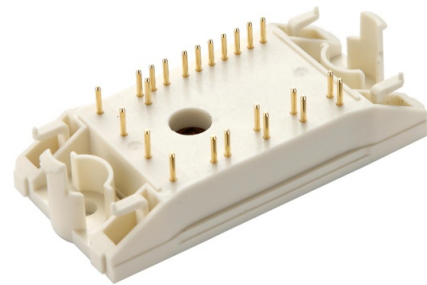
IGBT

GD10PJK120F1S

1200V/10A PIM in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.



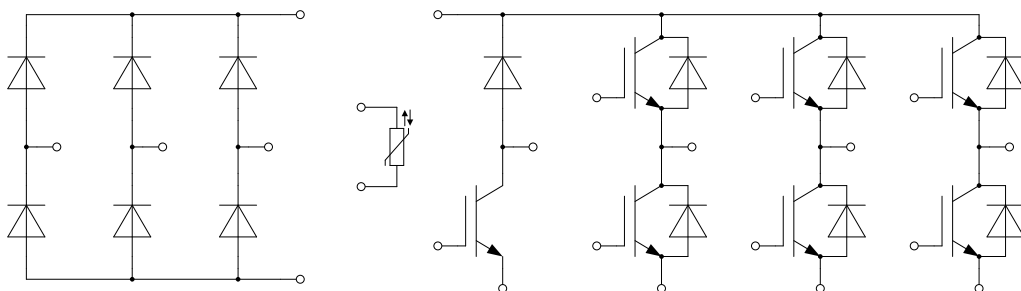
Features

- NPT IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 150°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated heatsink using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT-inverter**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	20	A
	@ $T_C=100^{\circ}\text{C}$	10	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	20	A
P_D	Maximum Power Dissipation @ $T_j=150^{\circ}\text{C}$	100	W

Diode-inverter

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	10	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	20	A

Diode-rectifier

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1600	V
I_O	Average Output Current 50Hz/60Hz,sine wave	10	A
I_{FSM}	Surge Forward Current $V_R=0\text{V}, t_p=10\text{ms}, T_j=45^{\circ}\text{C}$	270	A
I^2t	I^2t -value, $V_R=0\text{V}, t_p=10\text{ms}, T_j=45^{\circ}\text{C}$	360	A^2s

IGBT-brake

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	20	A
	@ $T_C=100^{\circ}\text{C}$	10	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	20	A
P_D	Maximum Power Dissipation @ $T_j=150^{\circ}\text{C}$	100	W

Diode-brake

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	10	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	20	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	150	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +125	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	4000	V

IGBT-inverter Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		2.15	2.60	V	
		$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		2.65			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=1.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.4	6.1	6.8	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			/		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		0.65		nF	
C_{res}	Reverse Transfer Capacitance				0.04		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.11		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		164		ns	
t_r	Rise Time			54		ns	
$t_{d(off)}$	Turn-Off Delay Time			238		ns	
t_f	Fall Time			352		ns	
E_{on}	Turn-On Switching Loss			2.18		mJ	
E_{off}	Turn-Off Switching Loss			0.72		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		168		ns
t_r	Rise Time				55		ns
$t_{d(off)}$	Turn-Off Delay Time			247		ns	
t_f	Fall Time			438		ns	
E_{on}	Turn-On Switching Loss			2.48		mJ	
E_{off}	Turn-Off Switching Loss			0.97		mJ	
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$			80		A

Diode-inverter Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.85	2.30	V
		$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		2.05		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=210\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		0.7		μC
I_{RM}	Peak Reverse Recovery Current			7		A
E_{rec}	Reverse Recovery Energy			0.31		mJ
Q_r	Recovered Charge			1.4		μC
I_{RM}	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=210\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		9		A
E_{rec}	Reverse Recovery Energy			0.51		mJ

Diode-rectifier Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		0.88		V
I_R	Reverse Current	$T_j=150^\circ\text{C}, V_R=1600\text{V}$			1.0	mA

IGBT-brake Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		2.15	2.60	V	
		$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		2.65			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=1.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.4	6.1	6.8	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			/		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		0.65		nF	
C_{res}	Reverse Transfer Capacitance				0.04		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.11		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		164		ns	
t_r	Rise Time				54		ns
$t_{d(off)}$	Turn-Off Delay Time				238		ns
t_f	Fall Time				352		ns
E_{on}	Turn-On Switching Loss				2.18		mJ
E_{off}	Turn-Off Switching Loss				0.72		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		168		ns	
t_r	Rise Time				55		ns
$t_{d(off)}$	Turn-Off Delay Time				247		ns
t_f	Fall Time				438		ns
E_{on}	Turn-On Switching Loss				2.48		mJ
E_{off}	Turn-Off Switching Loss				0.97		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		80		A	

Diode-brake Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.85	2.30	V
		$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		2.05		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=210\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		0.7		μC
I_{RM}	Peak Reverse Recovery Current			7		A
E_{rec}	Reverse Recovery Energy			0.31		mJ
Q_r	Recovered Charge			1.4		μC
I_{RM}	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=210\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		9		A
E_{rec}	Reverse Recovery Energy			0.51		mJ

NTC Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			22.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of R_{100}	$T_C=100^\circ\text{C}, R_{100}=1486.1\Omega$	-5		5	%
P_{25}	Power Dissipation				200	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		4000		K

Module Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Junction-to-Case (per IGBT-inverter)		1.135	1.248	K/W
	Junction-to-Case (per Diode-inverter)		2.223	2.445	
	Junction-to-Case (per Diode-rectifier)		1.326	1.459	
	Junction-to-Case (per IGBT-brake)		1.135	1.248	
	Junction-to-Case (per Diode-brake)		2.223	2.445	
R_{thCH}	Case-to-Heatsink (per IGBT-inverter)		0.550		K/W
	Case-to-Heatsink (per Diode-inverter)		1.077		
	Case-to-Heatsink (per Diode-rectifier)		0.643		
	Case-to-Heatsink (per IGBT-brake)		0.550		
	Case-to-Heatsink (per Diode-brake)		1.077		
	Case-to-Sink (per Module)		0.035		
M	Mounting Torque, Screw M4	2.0		2.2	N.m
G	Weight of Module		26		g

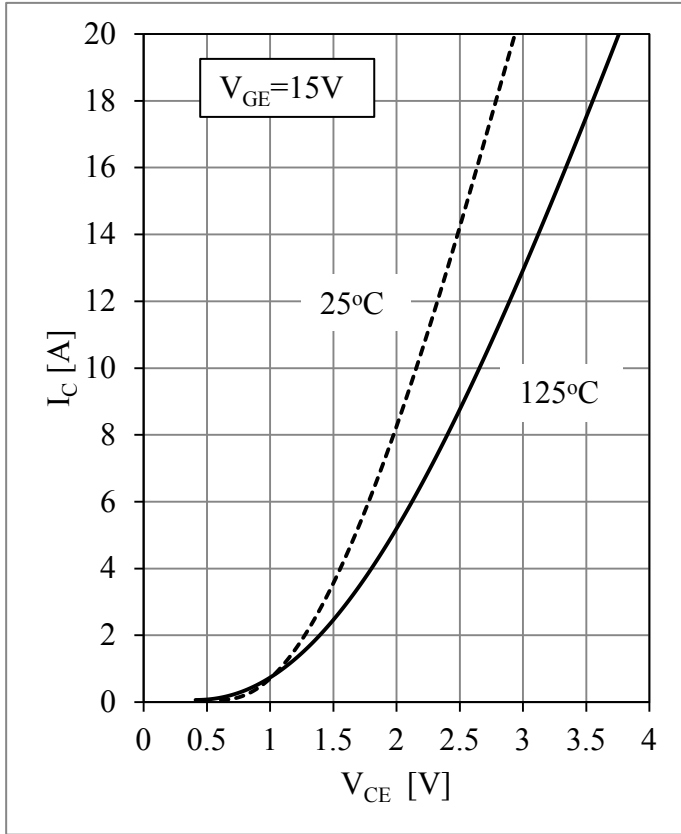


Fig 1. IGBT-inverter Output Characteristics

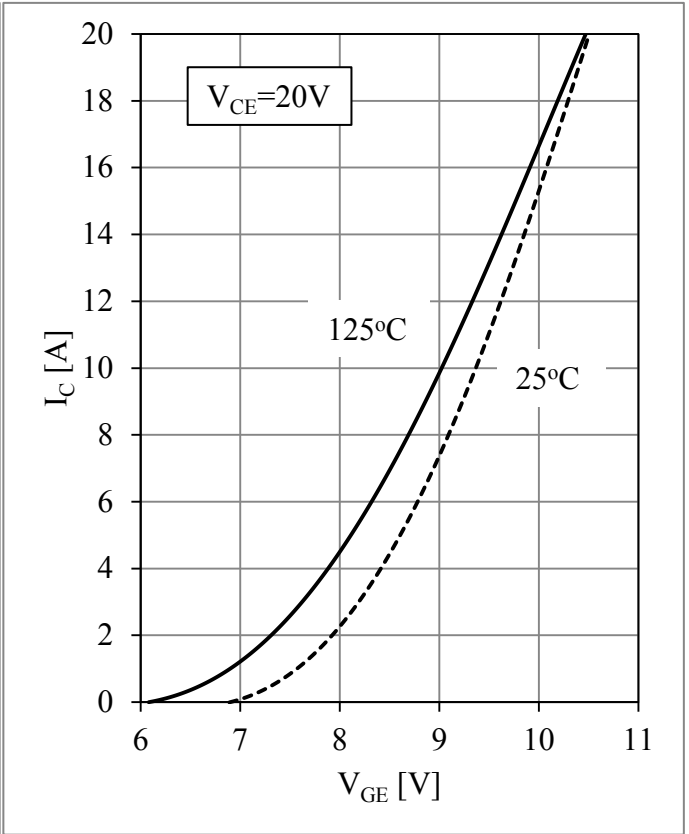


Fig 2. IGBT-inverter Transfer Characteristics

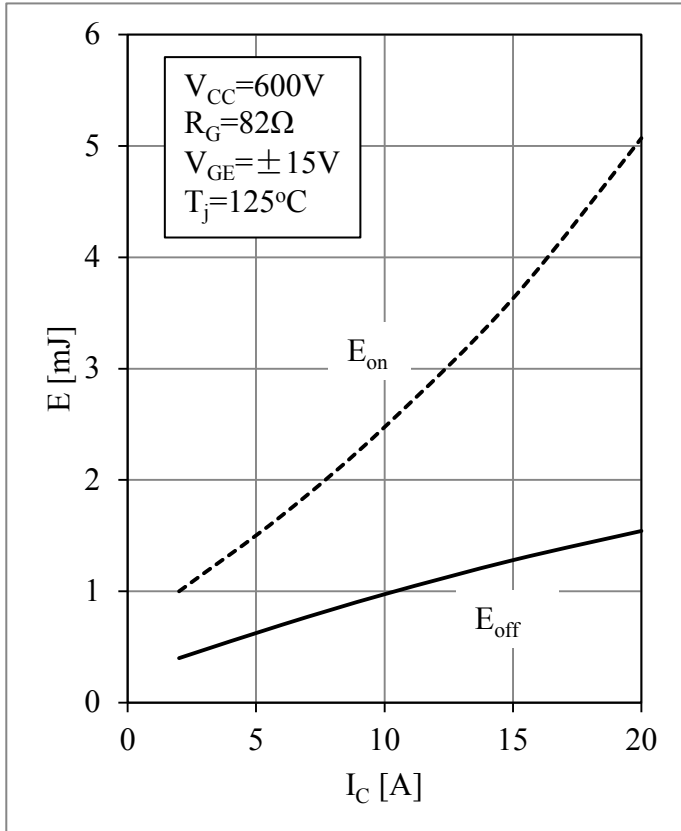


Fig 3. IGBT-inverter Switching Loss vs. I_C

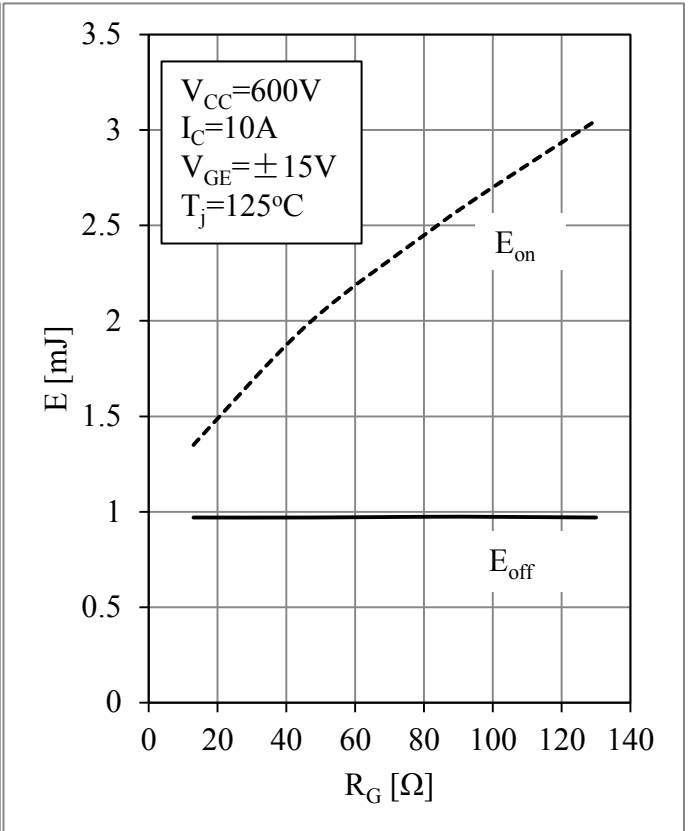


Fig 4. IGBT-inverter Switching Loss vs. R_G

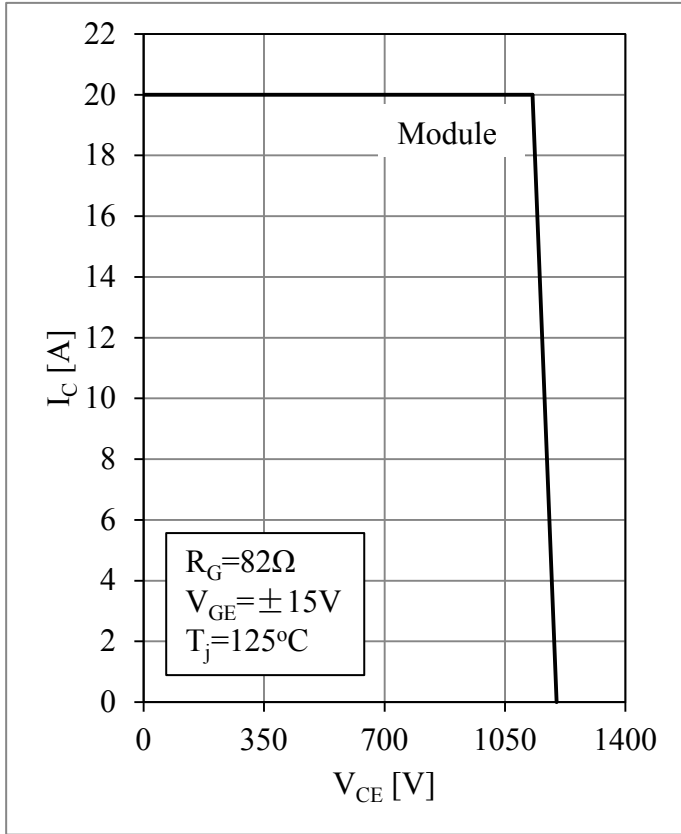


Fig 5. IGBT-inverter RBSOA

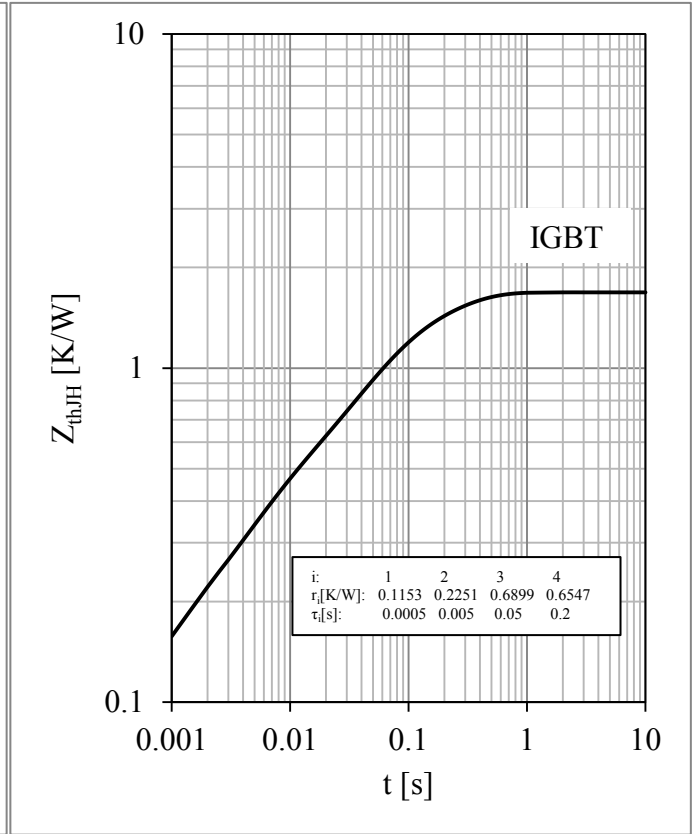


Fig 6. IGBT-inverter Transient Thermal Impedance

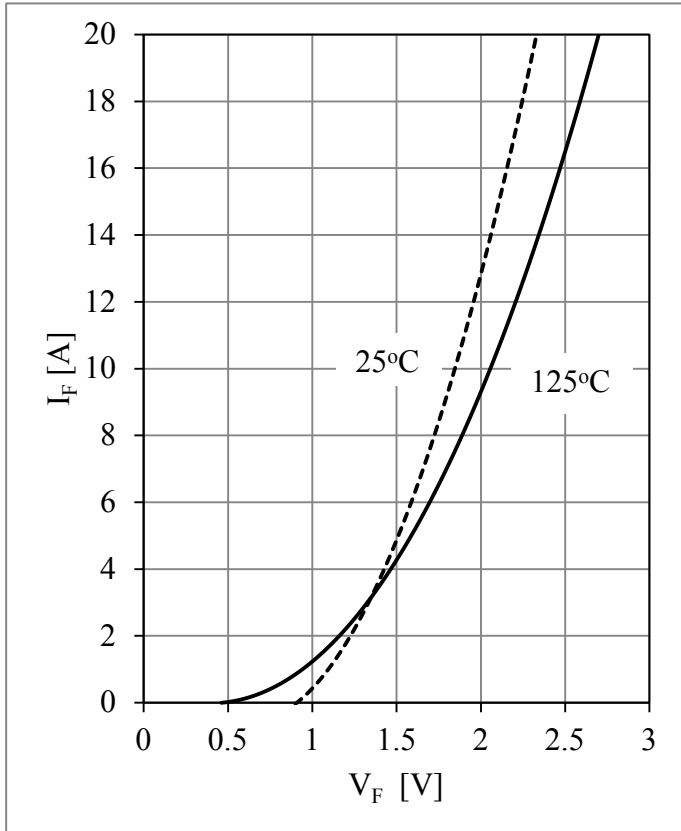


Fig 7. Diode-inverter Forward Characteristics

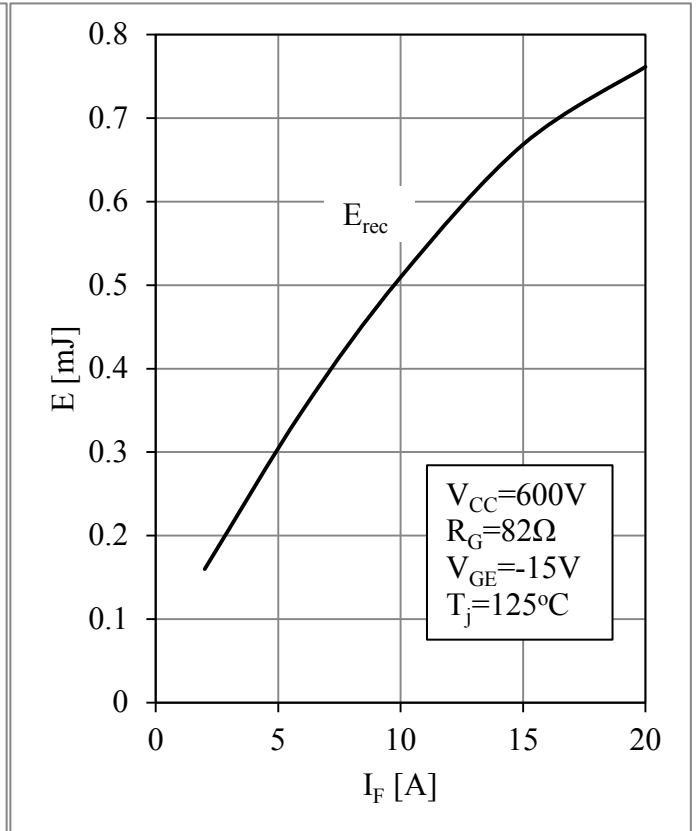


Fig 8. Diode-inverter Switching Loss vs. I_F

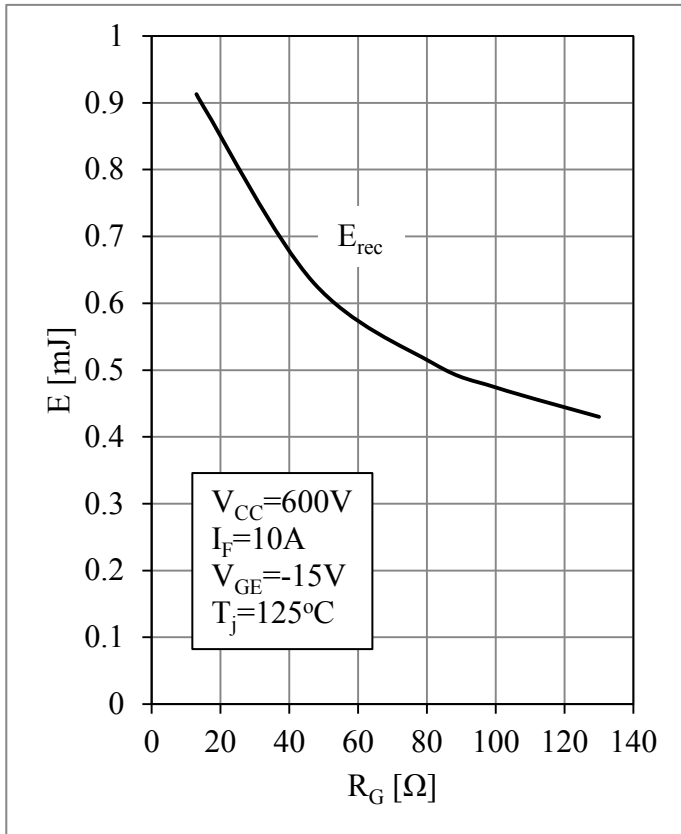


Fig 9. Diode-inverter Switching Loss vs. R_G

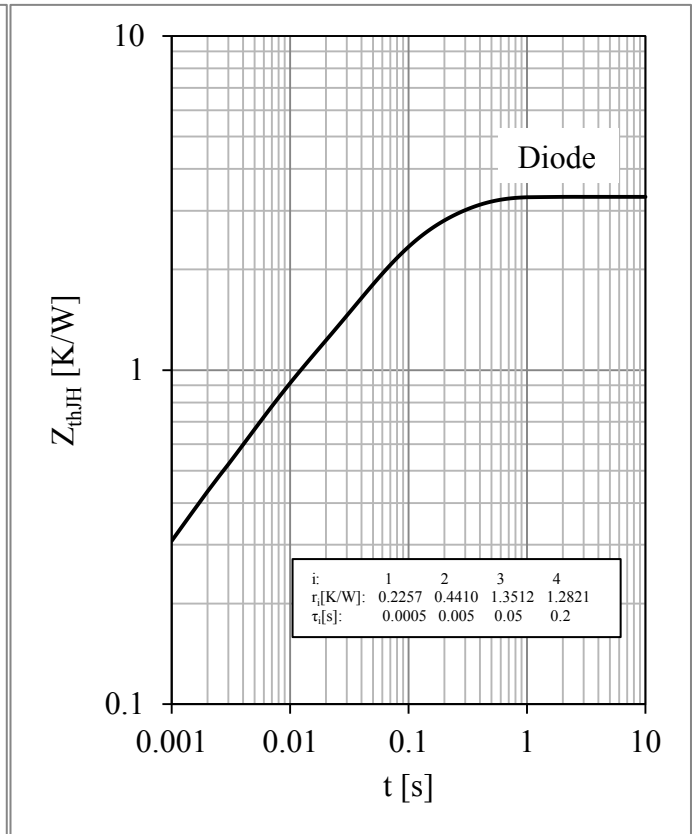


Fig 10. Diode-inverter Transient Thermal Impedance

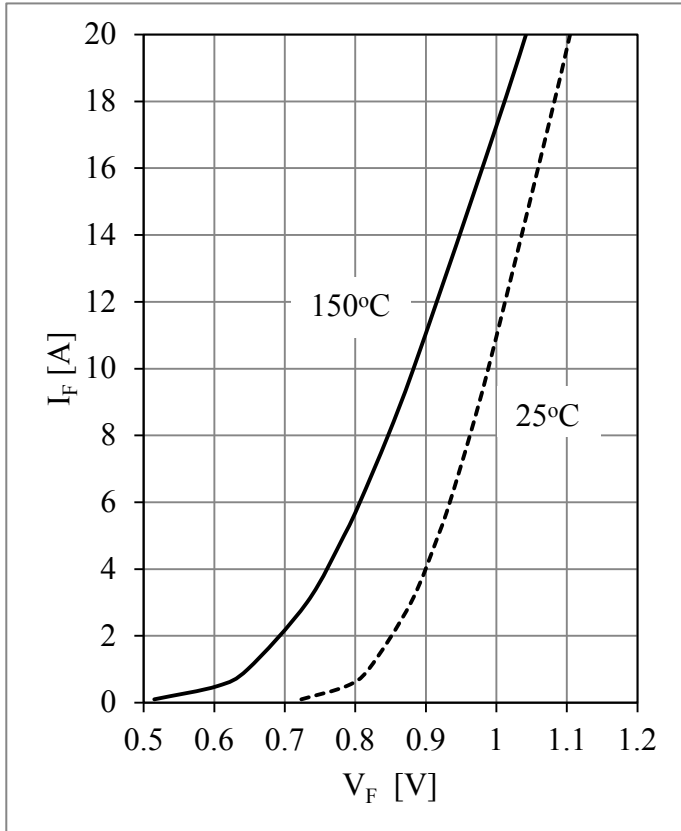


Fig 11. Diode-rectifier Forward Characteristics

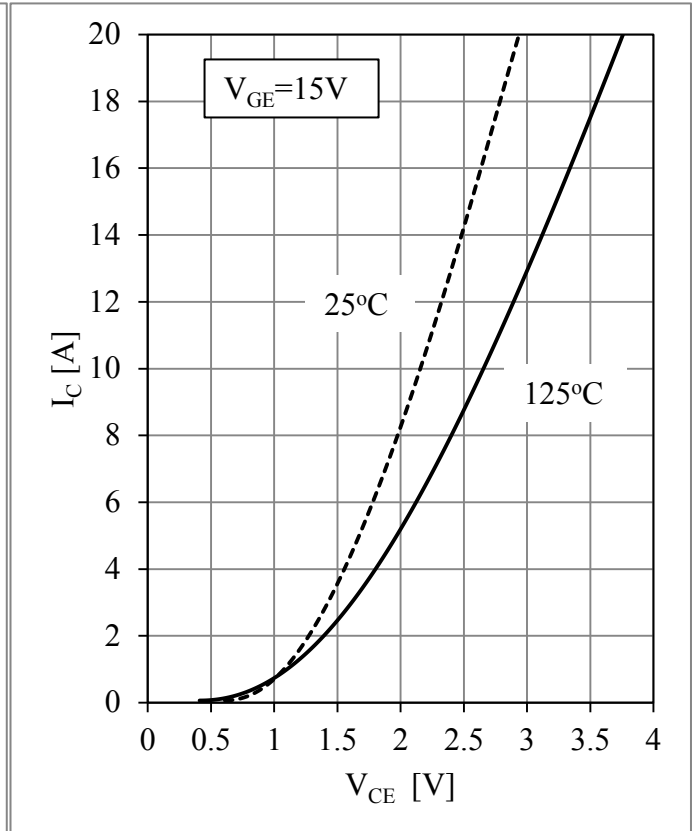


Fig 12. IGBT-brake Output Characteristics

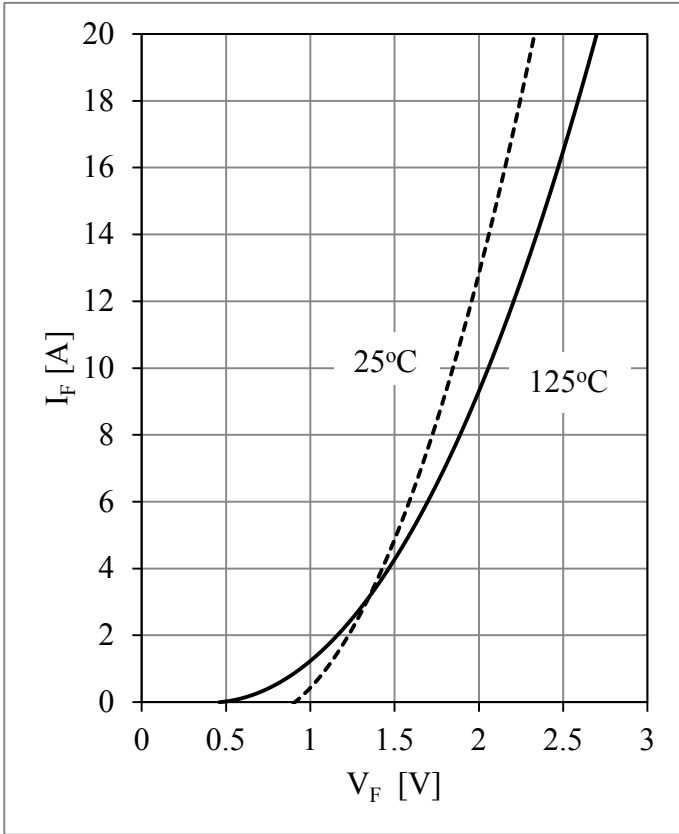


Fig 13. Diode-brake Forward Characteristics

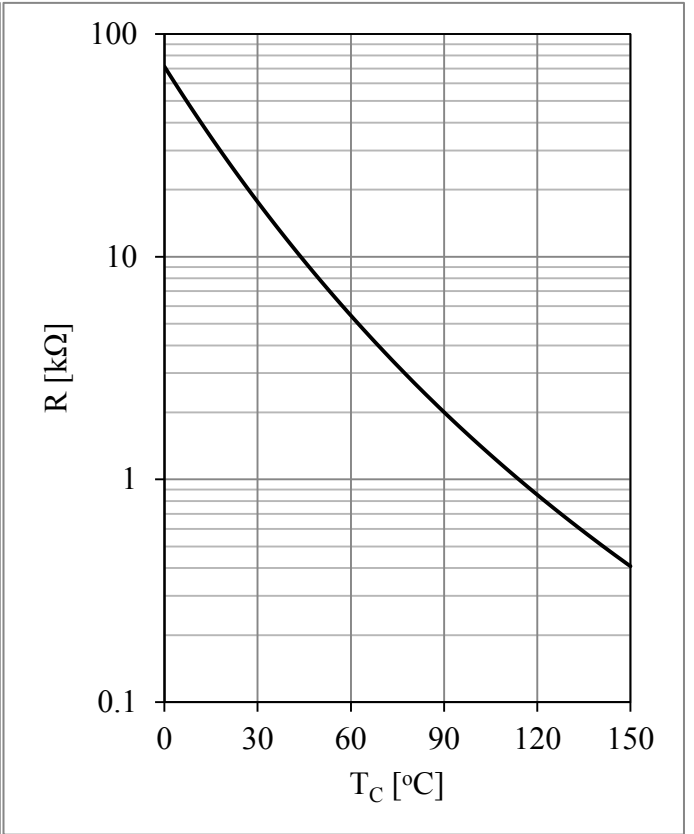
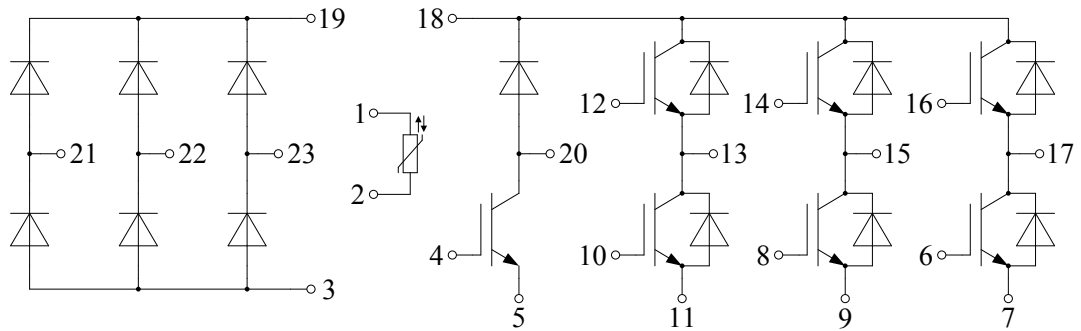


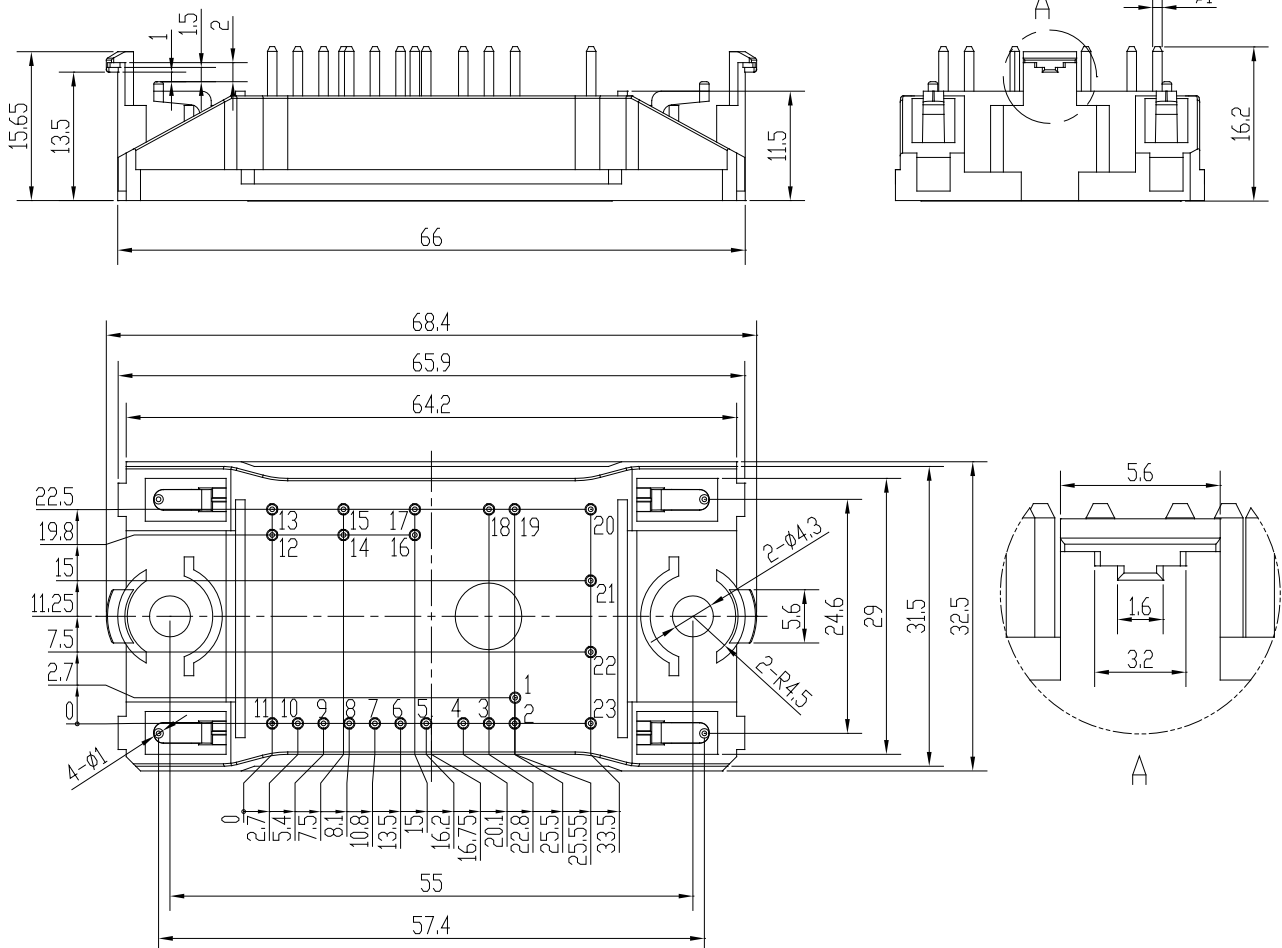
Fig 14. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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